

■ HIGH SPEED 2K X 8 DUAL-PORT STATIC RAM WITH INTERRUPTS

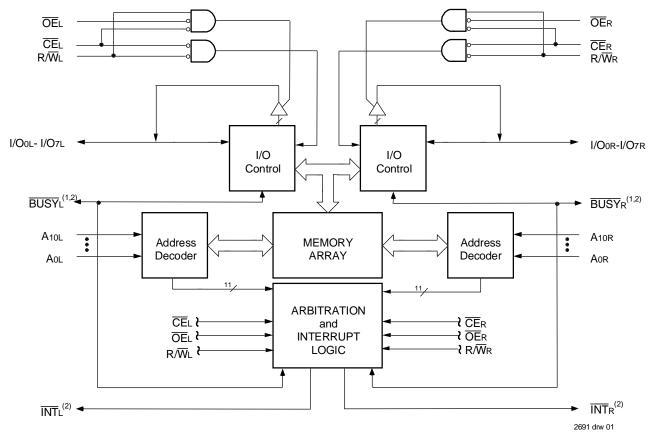
IDT71321SA/LA IDT71421SA/LA

Features

- High-speed access
 - Commercial: 20/25/35/55ns (max.)
 - Industrial: 55ns (max.)
- Low-power operation
 - IDT71321/IDT71421SA
 Active: 325mW (typ.)
 - Standby: 5mW (typ.)
 - IDT71321/421LA Active: 325mW (typ.) Standby: 1mW (typ.)
- ◆ Two INT flags for port-to-port communications

- MASTER IDT71321 easily expands data bus width to 16-ormore-bits using SLAVE IDT71421
- On-chip port arbitration logic (IDT71321 only)
- ◆ BUSY output flag on IDT71321; BUSY input on IDT71421
- Fully asynchronous operation from either port
- Battery backup operation 2V data retention (LA only)
- ◆ TTL-compatible, single 5V ±10% power supply
- ◆ Available in 52-Pin PLCC, 64-Pin TQFP, and 64-Pin STQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds

Functional Block Diagram



NOTES:

- IDT71321 (MASTER): BUSY is open drain output and requires pullup resistor of 270Ω. IDT71421 (SLAVE): BUSY is input.
- 2. Open drain output: requires pullup resistor of $270\Omega.$

MARCH 1999

Description

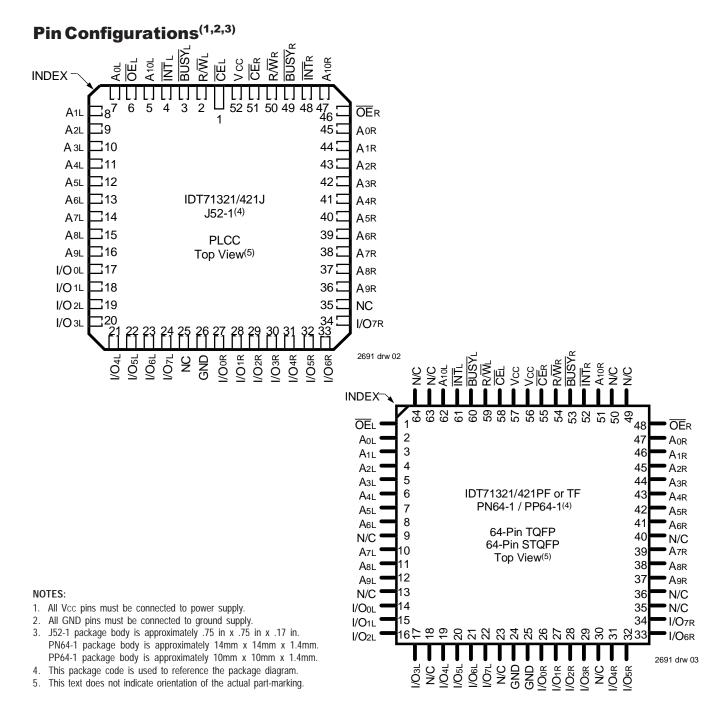
The IDT71321/IDT71421 are high-speed 2K x 8 Dual-Port Static RAMs with internal interrupt logic for interprocessor communications. The IDT71321 is designed to be used as a stand-alone 8-bit Dual-Port Static RAM or as a "MASTER" Dual-Port Static RAM together with the IDT71421 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port Static RAM approach in 16-or-more-bit memory system applications results in full speed, error-free operation without the need for additional discrete logic.

Both devices provide two independent ports with separate control,

address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by $\overline{\text{CE}}$, permits the on chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT71321/IDT71421 devices are packaged in 52-pin PLCCs, 64-pin TQFPs, and 64-pin STQFPs.



Capacitance⁽¹⁾

(TA = +25°C, f = 1.0MHz) TQFP Only

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF
				2691 tbl 00

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 2. 3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

2691 tbl 02

NOTES:

- 1. This is the parameter Ta.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	٧
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-55 to +125	۰C
Іоит	DC Output Current	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS
 may cause permanent damage to the device. This is a stress rating only
 and functional operation of the device at these or any other conditions
 above those indicated in the operational sections of the specification is not
 implied. Exposure to absolute maximum rating conditions for extended
 periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

2691 tbl 03

NOTES:

2691 tbl 01

- 1. VIL (min.) = -1.5V for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating
Temperature and Supply Voltage Range^(1,4,6) (Vcc = 5.0V ± 10%)

		(ros			7142	1X20 1X20 Only		1X25 1X25 Only	
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	\overline{CE} L and \overline{CE} R = VIL, Outputs Open f = fMAX ⁽²⁾	COM'L	SA LA	110 110	250 200	110 110	220 170	mA
	(DUIII PUIIS ACTIVE)	= [MAX ⁽²⁾	IND	SA LA	П			П	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	\overline{CE} L and \overline{CE} R = VIH f = fMAX $^{(2)}$	COM'L	SA LA	30 30	65 45	30 30	65 45	mA
	Level lilpuis)		IND	SA LA	11	_		1 1	
ISB2	Standby Current (One Port - TTL	CE'A" = VIL and CE'B" = VIH ⁽⁵⁾ Active Port Outputs Open,	COM'L	SA LA	65 65	165 125	65 65	150 115	mA
	Level Inputs)	f=fmax ⁽²⁾	IND	SA LA		_			
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CE and CER ≥ Vcc - 0.2V,	COM'L	SA LA	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Civios Level ilipuis)	$\sqrt{N} \ge VCC - 0.2V$ or $\sqrt{N} \le 0.2V$, $f = 0^{(2)}$	IND	SA LA				_	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	$\overline{CE}^{A^*} \leq 0.2V$ and $\overline{CE}^{B^*} \geq Vcc \cdot 0.2V^{(5)}$	COM'L	SA LA	60 60	155 115	60 60	145 105	mA
	Civios Level Ilipuis)	V in $\geq \overline{V}$ cc - 0.2 V or V in $\leq 0.2V$ Active Port Outputs Open, $f = f_{MAX}^{(2)}$	IND	SA LA					

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					7142	1X35 1X35 Only	7132 7142 Co & I	1X55 m'l	
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	\overline{CE} L and \overline{CE} R = VIL, Outputs Open f = fmax ⁽²⁾	COM'L	SA LA	80 80	165 120	65 65	155 110	mA
	(DUIII FUIIS ACTIVE)	I = IMAX**	IND	SA LA			65 65	190 140	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	\overline{CE} L and \overline{CE} R = VIH f = f _{MAX} (2)	COM'L	SA LA	25 25	65 45	20 20	65 35	mA
	Level inpuis)		IND	SA LA			20 20	65 45	
ISB2	Standby Current (One Port - TTL	CE'a" = VIL and CE'B" = VIH ⁽⁵⁾ Active Port Outputs Open, f=Mmx ⁽²⁾	COM'L	SA LA	50 50	125 90	40 40	110 75	mA
	Level Inputs)	T=IMAX [€] /	IND	SA LA			40 40	125 90	
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CE ₁ and CE _R ≥ Vcc - 0.2V,	COM'L	SA LA	1.0 0.2	15 4	1.0 0.2	15 4	mA
	CWOS Level lipus)	$/$ IN \geq VCC - 0.2V or $/$ IN \leq 0.2V, f = 0 ⁽³⁾	IND	SA LA			1.0 0.2	30 10	
ISB4	Full Standby Current (One Port -	$\overline{CE}_{B^*} \leq 0.2V$ and $\overline{CE}_{B^*} \geq Vcc \cdot 0.2V^{(5)}$	COM'L	SA LA	45 45	110 85	40 40	100 70	mA
	CMOS Level Inputs)	V N \geq V CC - $0.2V$ or V N \leq $0.2V$ Active Port Outputs Open, $f = f$ f f f f f f f f f	IND	SA LA		_	40 40	110 85	

NOTES:

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC TEST CONDITIONS" of input levels of GND to 3V
- 3. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 4. Vcc = 5V, Ta=+25°C for Typ and is not production tested. $Vcc \ DC = 100mA$ (Typ)
- 5. Port "A" may be either left or right port. Port "B" is opposite from port "A".
- 6. Industrial temperature: for other speeds, packages and powers contact your sales office.

2691 tbl 04b

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			71321SA 71421SA		7132 7142		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $VIN = 0V$ to Vcc	_	10	-	5	μA
lLO	Output Leakage Current ⁽¹⁾	$\overline{\overline{CE}} = V_{H}$, Vout = 0V to Vcc, Vcc - 5.5V		10		5	μA
Vol	Output Low Voltage (I/Oo-I/O7)	Iol = 4mA	_	0.4	-	0.4	V
Vol	Open Drain O <u>utput</u> Low Voltage (BUSY/INT)	IoL = 16mA		0.5		0.5	V
Voh	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	V

NOTE:

1. At $Vcc \le 2.0V$ leakages are undefined.

2691 tbl 05

2691 tbl 06

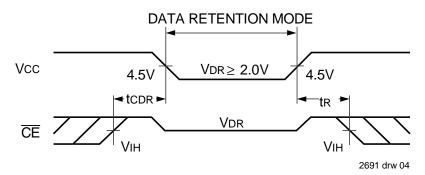
Data Retention Characteristics (LA Version Only)

Symbol	Parameter	Test Condition		Min.	Typ. ⁽¹⁾	Max.	Unit
Vdr	Vcc for Data Retention			2.0		0	V
ICCDR	Data Retention Current	$Vcc = 2.0V$, $\overline{CE} \ge Vcc - 0.2V$	COM'L	_	100	1500	μA
		$VIN \ge VCC - 0.2V$ or $VIN \le 0.2V$	IND	_	100	4000	μA
tcdr(3)	Chip Deselect to Data Retention Time			0	_	_	ns
tR ⁽³⁾	Operation Recovery Time			trc ⁽²⁾			ns

NOTES:

- 1. Vcc = 2V, TA = +25°C, and is not production tested.
- 2. trc = Read Cycle Time
- 3. This parameter is guaranteed but not production tested.

Data Retention Waveform



AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

2691 tbl 07

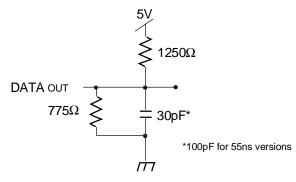


Figure 1. AC Output Test Load

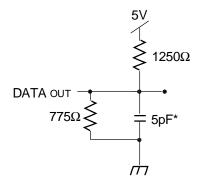
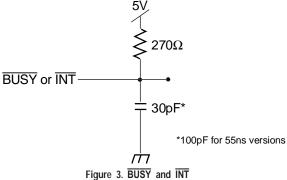


Figure 2. Output Test Load (for thz, tLz, twz, and tow) * Including scope and jig.



AC Output Test Load

2691 drw 05

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range^(2,4)

		71321X20 71421X20 Com'l Only		71321X25 71421X25 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
trc	Read Cycle Time	20		25	1	ns
taa	Address Access Time		20	_	25	ns
tace	Chip Enable Access Time	_	20		25	ns
taoe	Output Enable Access Time		11	_	12	ns
tон	Output Hold from Address Change	3		3	1	ns
t LZ	Output Low-Z Time ^(1,3)	0	_	0	_	ns
tHZ	Output High-Z Time ^(1,3)	_	10	-	10	ns
tpu	Chip Enable to Power Up Time ⁽³⁾	0	_	0	_	ns
tPD	Chip Disable to Power Down Time ⁽³⁾	_	20		25	ns

2691 tbl 08a

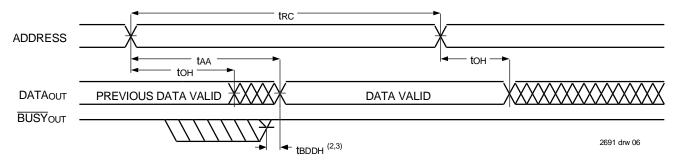
		71321X35 71421X35 Com'l Only		71321X55 71421X55 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
trc	Read Cycle Time	35	_	55	_	ns
taa	Address Access Time	_	35	_	55	ns
tace	Chip Enable Access Time	_	35	_	55	ns
taoe	Output Enable Access Time	_	20	-	25	ns
tон	Output Hold from Address Change	3		3	_	ns
t LZ	Output Low-Z Time ^(1,3)	0	-	5	_	ns
tHZ	Output High-Z Time ^(1,3)	_	15	_	25	ns
tru	Chip Enable to Power Up Time ⁽³⁾	0	_	0	_	ns
t PD	Chip Disable to Power Down Time ⁽³⁾		35	_	50	ns

NOTES:

- 1. Transition is measured ±500mV from Low or High-impedance voltage Output Test Load (Figure 2).
- 2. 'X' in part numbers indicates power rating (SA or LA).
- 3. This parameter is guaranteed by device characterization, but is not production tested.
- 4. Industrial temperature: for other speeds, packages and powers contact your sales office.

2691 tbl 08b

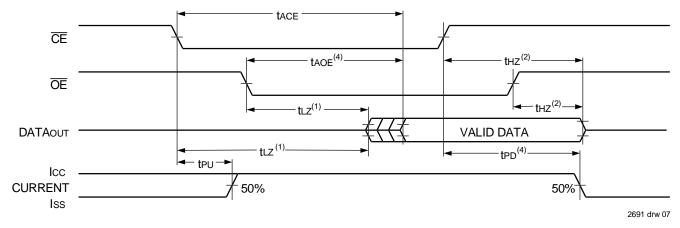
Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾



NOTES:

- 1. $R\overline{W} = V_{IH}$, $\overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbdd delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

Timing Waveform of Read Cycle No. 2, Either Side (3)



NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. $R\overline{W} = VIH$ and $\overline{OE} = VIL$, and the address is valid prior to or coincidental with \overline{CE} transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tage, ta

AC Electrical Characteristics Over the Operating Temeprature and Supply Voltage Range^(4,5)

		71321X20 71421X20 Com'l Only		7132 7142 Com'						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
WRITE CYCLE										
twc	Write Cycle Time ⁽²⁾	20	_	25	_	ns				
tew	Chip Enable to End-of-Write	15	_	20	_	ns				
taw	Address Valid to End-of-Write	15	_	20	_	ns				
tas	Address Set-up Time	0	_	0	_	ns				
t WP	Write Pulse Width ⁽³⁾	15	_	15	_	ns				
twr	Write Recovery Time	0	_	0	_	ns				
tow	Data Valid to End-of-Write	10	_	12	_	ns				
tHZ	Output High-Z Time ⁽¹⁾	_	10	_	10	ns				
tон	Data Hold Time	0		0		ns				
twz	Write Enable to Output in High-Z ⁽¹⁾	_	10	_	10	ns				
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0	_	ns				

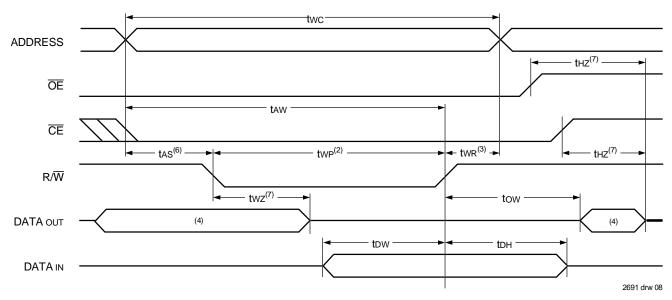
2691 tbl 09a

		7142	1X35 1X35 Only	7132 7142 Com'l		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE						
twc	Write Cycle Time ⁽²⁾	35	_	55	_	ns
tew	Chip Enable to End-of-Write	30	_	40	_	ns
taw	Address Valid to End-of-Write	30	_	40	_	ns
tas	Address Set-up Time	0	_	0	_	ns
twp	Write Pulse Width ⁽³⁾	25	_	30	_	ns
twr	Write Recovery Time	0	_	0	_	ns
tow	Data Valid to End-of-Write	15	_	20	_	ns
tHZ	Output High-Z Time ⁽¹⁾	_	15	_	25	ns
tDH	Data Hold Time	0		0	_	ns
twz	Write Enable to Output in High-Z ⁽¹⁾	_	15	_	30	ns
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0	_	ns

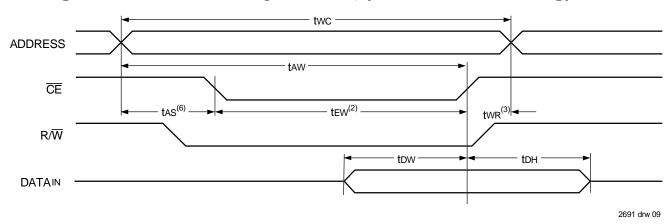
NOTES:

- 2691 tbl 09b
- Transition is measured ±500mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.
- 2. For Master/Slave combination, two = tbaa + twp, since $R\overline{W} = V_{IL}$ must occur after tbaa .
- 3. If \overline{OE} is LOW during a R/ \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R/ \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 4. 'X' in part numbers indicates power rating (SA or LA).
- 5. Industrial temperature: for other speeds, packages and powers contact your sales office.

Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)(1,5,8)



Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)(1,5)



NOTES:

- 1. $R\overline{W}$ or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of \overline{CE} = V_{IL} and R/W= V_{IL}.
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or R/\overline{W} going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined to be device characterization, but is not production tested. Transition is measured ±500mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during a R \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(6,7)

		7142	21X20 21X20 I Only	71321X25 71421X25 Com'l Only			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
BUSY TIMING	(For MASTER 71321)						
tbaa	BUSY Access Time from Address		20	_	20	ns	
t BDA	BUSY Disable Time from Address	_	20	_	20	ns	
†BAC	BUSY Access Time from Chip Enable	_	20	_	20	ns	
tBDC	BUSY Disable Time from Chip Enable		20	_	20	ns	
twn	Write Hold After BUSY ⁽⁵⁾	12		15		ns	
twdd	Write Pulse to Data Delay ⁽¹⁾		50	_	50	ns	
todd	Write Data Valid to Read Data Delay ⁽¹⁾		35	_	35	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5	_	ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾		25	_	35	ns	
BUSY INPUT 1	IMING (For SLAVE 71421)						
twB	Write to BUSY Input ⁽⁴⁾	0		0	_	ns	
twn	Write Hold After BUSY ⁽⁵⁾	12		15		ns	
twdd	Write Pulse to Data Delay ⁽¹⁾		40	_	50	ns	
todd	Write Data Valid to Read Data Delay ⁽¹⁾		30	_	35	ns	

2691 tbl 10a

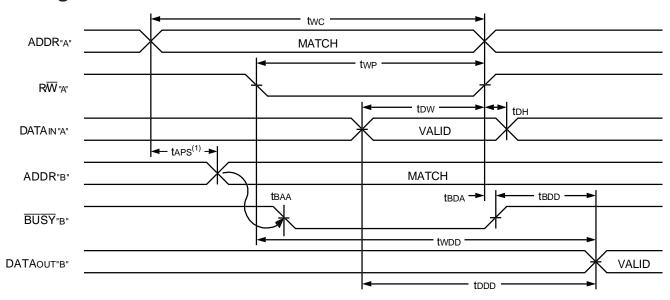
2691 tbl 10b

		7142	1X35 1X35 Only	71321X55 71421X55 Com'l & Ind						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
BUSY TIMING	(For MASTER 71321)									
tbaa	BUSY Access Time from Address	_	20	_	30	ns				
tbda	BUSY Disable Time from Address	I	20	I	30	ns				
tBAC	BUSY Access Time from Chip Enable	_	20	_	30	ns				
tbdc	BUSY Disable Time from Chip Enable		20	_	30	ns				
twн	Write Hold After $\overline{BUSY}^{(5)}$	20		20		ns				
twdd	Write Pulse to Data Delay ⁽¹⁾	_	60	_	80	ns				
todd	Write Data Valid to Read Data Delay ⁽¹⁾	_	35		55	ns				
taps	Arbitration Priority Set-up Time (2)	5	-	5	-	ns				
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	35	_	50	ns				
BUSY INPUT T	BUSY INPUT TIMING (For SLAVE 71421)									
twB	Write to BUSY Input ⁽⁴⁾	0		0		ns				
twн	Write Hold After BUSY ⁽⁵⁾	20		20		ns				
twdd	Write Pulse to Data Delay ⁽¹⁾	_	60	_	80	ns				
todd	Write Data Valid to Read Data Delay ⁽¹⁾		35	_	55	ns				

NOTES

- 1. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY."
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 4. To ensure that a write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 6. 'X' in part numbers indicates power rating (SA or LA).
- 7. Industrial temperature: for other speeds, packages and powers contact your sales office.

Timing Waveform of Write with Port-to-Port Read and BUSY (2,3,4)

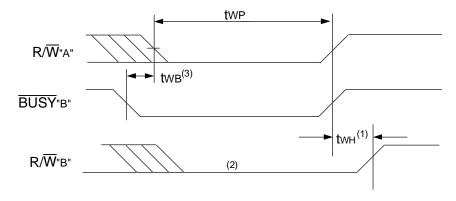


NOTES:

2691 drw 10

- 1. To ensure that the earlier of the two ports wins. taps is ignored for Slave (71421).
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of Write with BUSY⁽⁴⁾

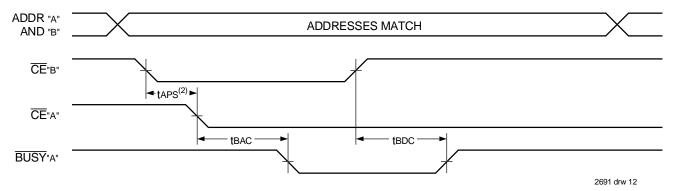


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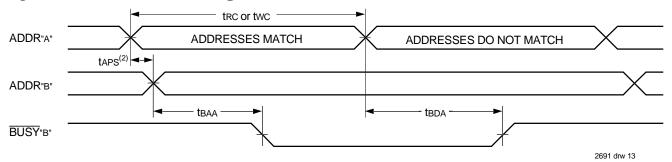
2691 drw 11

- 1. $\underline{\text{tw}}$ H must be met for both $\overline{\text{BUSY}}$ input (71421, slave) or output (71321, Master).
- 2. BUSY is asserted on port "B" blocking RW"B", until BUSY"B" goes HIGH.
- 3. twb is only for the slave version (71421).
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of BUSY Arbitration Controlled by CE Timing(1)



Timing Waveform of \overline{BUSY} Arbritration Controlled by Address Match Timing⁽¹⁾



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (71321 only).

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,2)

sperating remperature and suppry voltage hange										
		71321X20 71421X20 Com'l Only		71321X25 71421X25 Com'l Only						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
INTERRUPT	TIMING									
tas	Address Set-up Time	0	_	0	_	ns				
twr	Write Recovery Time	0	_	0	_	ns				
tins	Interrupt Set Time	_	20	_	25	ns				
tinr	Interrupt Reset Time	_	20		25	ns				

NOTES

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. Industrial temperature: for other speeds, packages and powers contact your sales office.

2691 tbl 11a

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range^(1,2)

		71321X35 71421X35 Com'l Only		7132 7142 Co &						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
INTERRUPT 1	INTERRUPT TIMING									
tas	Address Set-up Time	0	_	0	_	ns				
twr	Write Recovery Time	0	_	0	_	ns				
tins	Interrupt Set Time	_	25	_	45	ns				
tinr	Interrupt Reset Time	_	25	_	45	ns				

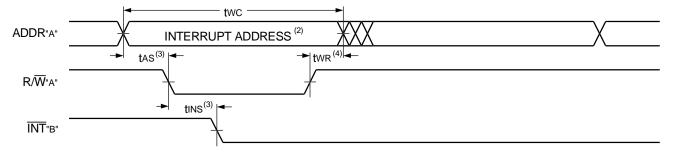
NOTES:

2691 tbl 11b

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. Industrial temperature: for other speeds, packages and powers contact your sales office.

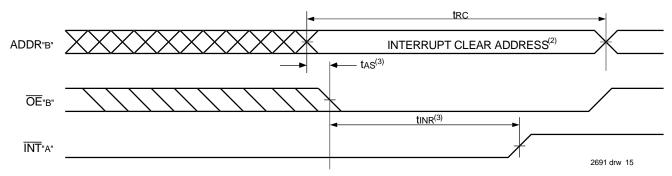
Timing Waveform of Interrupt Mode⁽¹⁾

SET INT



2691 drw 14

CLEAR INT



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table.
- Timing depends on which enable signal (CE or RW) is asserted last.
 Timing depends on which enable signal (CE or RW) is de-asserted first.

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Truth Tables

Truth Table I. Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port ⁽¹⁾				
R/W	CE	ŌĒ	D ₀₋₇	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	CER = CEL = VH, Power-Down Mode, ISB1 or ISB3
L	L	Χ	DATAIN	Data on Port Written Into Memory ⁽²⁾
Н	L	L	DATAоит	Data in Memory Output on Port ⁽³⁾
Н	L	Н	Z	High Impedance Outputs

NOTES: 2691 tbl 12

- 1. $A_{0L} A_{10L} \neq A_{0R} A_{10R}$.
- 2. If $\overline{\text{BUSY}} = \text{L}$, data is not written.
- 3. If $\overline{BUSY} = L$, data may not be valid, see two and too timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Truth Table II. Interrupt Flag^(1,4)

Left Port				Right Port						
R/WL	CEL	ŌĒL	A10L-A0L	ĪNTL	R/W̄R	CER	OE R	A10R-A0R	Ī NT R	Function
L	L	Х	7FF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INT _R Flag
Х	Х	Х	Х	Х	Х	L	L	7FF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FE	Х	Set Left INTL Flag
Х	L	L	7FE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

- 1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$
- 2. If $\overline{BUSY}_L = V_{IL}$, then No Change.
- 3. If $\overline{BUSY}R = VIL$, then No Change.
- 4. 'H' = HIGH, 'L' = LOW, 'X' = DON'T CARE

Truth Table III — Address BUSY Arbitration

	ln	puts	Out		
ŒL	C ER	Aol-A1ol Aor-A1or	BUSY _{L(1)}	BUSYR ⁽¹⁾	Function
Χ	Х	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

2691 tbl 14

- 1. Pins BUSYL and BUSYR are both outputs for 71321 (Master). Both are inputs for 71421 (Slave). BUSYx outputs on the 71321 are open drain, not push-pull outputs. On slaves the BUSYx input internally inhibits writes.
- 2. 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSY_L or BUSY_R = LOW will result. BUSY_L and BUSY_R outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT71321/IDT71421 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71321/IDT71421 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ = V_{I+}). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{\text{INT}}_L$) is asserted when the right port writes to memory location 7FE (HEX), where a write is defined as the $\overline{\text{CE}}_R = R/\overline{W}_R = V_{IL}$, per Truth Table II. The left port clears the interrupt by accessing address location 7FE when $\overline{\text{CE}}_L = \overline{\text{OE}}_L = V_{IL}$, R/W is a "don't care". Likewise, the right port interrupt flag ($\overline{\text{INT}}_R$) is asserted when the left port writes to memory location 7FF (HEX) and to clear the interrupt flag ($\overline{\text{INT}}_R$), the right port must access the memory location 7FF. The message (8 bits) at 7FE or 7FF is user-defined, since it is an addressable SRAMlocation. If the interrupt function is not used, address locations 7FE and 7FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation. In slave mode the \overline{BUSY} pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the \overline{BUSY} pins HIGH. If desired, unintended write operations can be prevented to a port by tying the \overline{BUSY} pin for that port LOW.

The BUSY outputs on the IDT71321 (Master) are open drain type outputs and require open drain resistors to operate. If these SRAMs are

being expanded in depth, then the BUSY indication for the resulting array does not require the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an SRAM array in width while using BUSY logic, one master part is used to decide which side of the SRAM array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the BUSY signal as a write inhibit signal. Thus on the IDT71321/IDT71421 SRAMs the BUSY pin is an output if the part is Master (IDT7132), and the BUSY pin is an input if the part is a Slave (IDT7142) as shown in Figure 3.

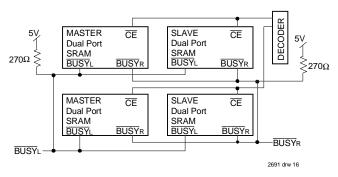
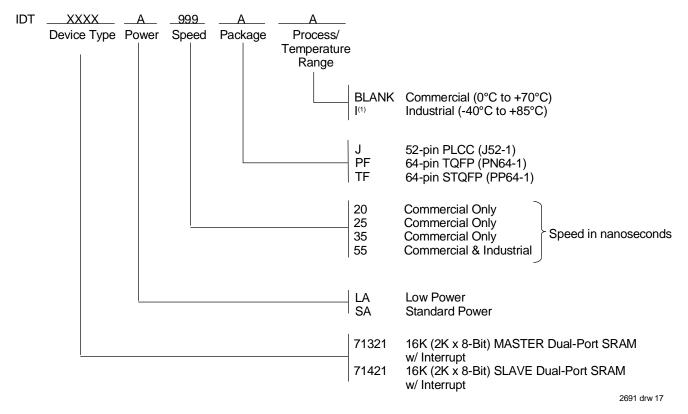


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT71321 (Master) and (Slave) IDT71421 SRAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating \overline{BUSY} on one side of the array and another master indicating \overline{BUSY} on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The \overline{BUSY} arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a \overline{BUSY} flag to be output from the master before the actual write pulse can be initiated with either the R/\overline{W} signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Ordering Information



NOTE:

Industrial temperature range is available in selected PLCC packages in standard power.
 For other speeds, packages and powers contact your sales office.

Datasheet Document History

3/24/99: Initiated datasheet document history

Converted to new format

Cosmetic typographical corrections

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